

L Number	Hits	Search Text	DB	Tim stamp
-	0	(trench same (hf or (hydrofluoric near a id)) same ((buff r d near xid near t hant) r boe) near10 about near10 seconds)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/25 11:33
-	0	trench same (hf or (hydrofluoric near acid)) same (((buffered near oxide near etchant) or boe) near10 about near10 seconds)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/25 11:34
-	7	(hf or (hydrofluoric near acid)) same (((buffered near oxide near etchant) or boe) near10 about near10 seconds)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/25 11:35
-	55	(hf or (hydrofluoric near acid)) same (((buffered near oxide near etchant) or boe) near10 seconds)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/25 11:35
-	3	trench same (hf or (hydrofluoric near acid)) same (((buffered near oxide near etchant) or boe) near10 seconds)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/25 11:35
-	46	(((buffered near oxide near etchant) or boe) near10 about near10 seconds)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/25 11:38
-	11	(((buffered near oxide near etchant) or boe) near10 about near10 seconds)) and trench	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/25 11:37
-	3	((((buffered near oxide near etchant) or boe) near10 about near10 seconds)) and trench) and (organic or inorganic)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/25 11:37
-	2	((((buffered near oxide near etchant) or boe) near10 about near10 seconds)) and trench) and (organic or inorganic)) and (wall or sidewall or (side near wall))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/25 11:37
-	3	(((buffered near oxide near etchant) or boe) near10 about near10 ec nds) and (parasitic near capacitance)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/25 11:39

-	217	(parasitic near capacitance) and oxide and (organic or inorganic) and (dielectric near constant) and trench and (wall or sidewall or (side near wall)) and (oxygen or oxygenating or oxygenated or oxygenation)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/25 11:41
-	211	(parasitic near capacitance) and oxide and (organic or inorganic) and (dielectric near constant) and trench and (wall or sidewall or (side near wall)) and (oxygen or oxygenating or oxygenated or oxygenation) and (etch or etching or etched or etchant)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/25 11:41
-	124	(parasitic near capacitance) and oxide and (organic or inorganic) and (dielectric near constant) and trench and (wall or sidewall or (side near wall)) and (oxygen or oxygenating or oxygenated or oxygenation) and (etch or etching or etched or etchant) and (hydrofluoric or boe or (buffered near oxide))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/25 11:41
-	10	(parasitic near capacitance) and oxide and (organic or inorganic) and (dielectric near constant) and trench and (wall or sidewall or (side near wall)) and (oxygen or oxygenating or oxygenated or oxygenation) and (etch or etching or etched or etchant) and (hydrofluoric or boe or (buffered near oxide)).ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/25 11:43
-	7	(parasitic near capacitance) and oxide.ti,ab,clm. and (organic or inorganic) and (dielectric near constant) and trench and (wall or sidewall or (side near wall)) and (oxygen or oxygenating or oxygenated or oxygenation) and (etch or etching or etched or etchant) and (hydrofluoric or boe or (buffered near oxide)).ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/25 11:43
-	5	(parasitic near capacitance) and oxide.ti,ab,clm. and (organic or inorganic) and (dielectric near constant) and trench and (wall or sidewall or (side near wall)) and (oxygen or oxygenating or oxygenated or oxygenation) and (etch or etching or etched or etchant) and (hydrofluoric or boe or (buffered near oxide)).ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/25 11:44
-	8	(parasitic near capacitance) and oxide and (organic or inorganic) and (dielectric near constant) and trench and (wall or sidewall or (side near wall)) and (oxygen or oxygenating or oxygenated or oxygenation) and (etch or etching or etched or etchant) and (hydrofluoric or boe or (buffered near oxide)).ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/25 11:44